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June 2014

FDA18N50

N-Channel UniFETTM MOSFET 500 V, 19 A, 265 m Ω

Features

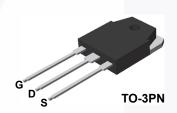
- $R_{DS(on)}$ = 265 m Ω (Max.) @ V_{GS} = 10 V, I_D = 9.5 A
- Low Gate Charge (Typ. 45 nC)
- Low C_{rss} (Typ. 25 pF)
- 100% Avalanche Tested

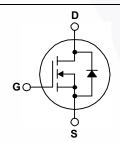
Applications

- PDP TV
- · Uninterruptible Power Supply
- · AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FDA18N50	Unit		
V _{DSS}	Drain-Source Voltage			500	V	
I _D	Drain Current	- Continuous (T _C = 25°C) - Continuous (T _C = 100°C)		19 11.4	A A	
I _{DM}	Drain Current	- Pulsed (Note 1)		76	Α	
V _{GSS}	Gate-Source voltage			±30	V	
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	945	mJ	
AR	Avalanche Current		(Note 1)	19	Α	
E _{AR}	Repetitive Avalanche Energy		(Note 1)	23	mJ	
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	4.5	V/ns	
P_{D}	Power Dissipation	(T _C = 25°C) - Derate above 25°C		239 1.92	W W/°C	
T _{J,} T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C		
TL	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C		

Thermal Characteristics

Symbol	Parameter	FDA18N50	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.52	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40		

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDA18N50	FDA18N50	TO-3PN	Tube	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions		Тур.	Max	Unit
Off Charac	teristics				1	
BV _{DSS}	Drain-Source Breakdown Voltage	age $V_{GS} = 0V, I_D = 250\mu A$				V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C		0.5		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500V, V _{GS} = 0V V _{DS} = 400V, T _C = 125°C			1 10	μ Α μ Α
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V	-		100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30V, V _{DS} = 0V			-100	nA
On Charac	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 9.5A		0.220	0.265	Ω
g _{FS}	Forward Transconductance	$V_{DS} = 40V, I_{D} = 9.5A$		25		S
Dynamic C	Characteristics			II.		
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V,	\	2200	2860	pF
C _{oss}	Output Capacitance	f = 1.0MHz		330	430	pF
C _{rss}	Reverse Transfer Capacitance			25	40	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time	V_{DD} = 250V, I_{D} = 19A R_{G} = 25 Ω (Note 4)		55	120	ns
t _r	Turn-On Rise Time			165	340	ns
t _{d(off)}	Turn-Off Delay Time			95	200	ns
t _f	Turn-Off Fall Time			90	190	ns
Qg	Total Gate Charge	V _{DS} = 400V, I _D = 19A	/	45	60	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10V (Note 4)		12.5		nC
Q _{gd}	Gate-Drain Charge			19		nC
Drain-Sour	rce Diode Characteristics and Maximur	m Ratings				
I _S Maximum Continuous Drain-Source Diode Forward Current					19	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				76	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 19A			1.4	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0V, I_S = 19A$ $dI_F/dt = 100A/\mu s$		500		ns
Q _{rr}	Reverse Recovery Charge			5.4		μС

NOTES:

- ${\it 1.} \ {\it Repetitive Rating: Pulse width limited by maximum junction temperature}$
- 2. L = 4.7mH, I $_{AS}$ = 19A, V $_{DD}$ = 50V, R $_{G}$ = 25 Ω , Starting T $_{J}$ = 25°C
- 3. $I_{SD} \le 19A$, di/dt $\le 200A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting T_J = $25^{\circ}C$
- 4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Characteristics

Figure 1. On-Region Characteristics

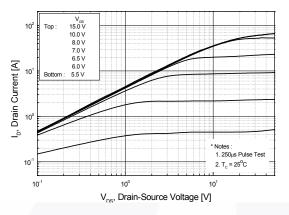


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

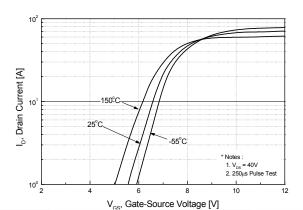


Figure 2. Transfer Characteristics

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

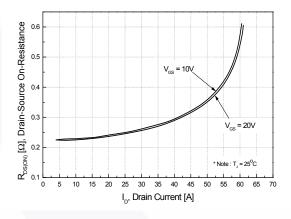


Figure 5. Capacitance Characteristics

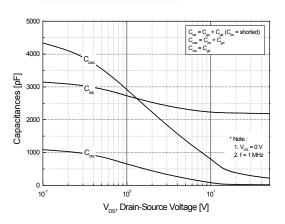
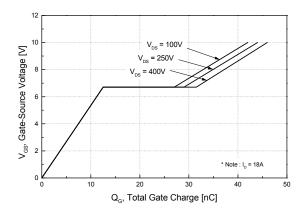


Figure 6. Gate Charge Characteristics



Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

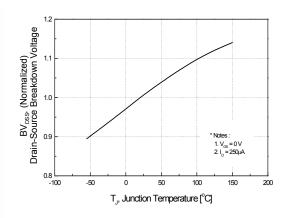


Figure 8. On-Resistance Variation vs. Temperature

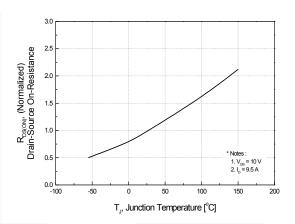


Figure 9. Maximum Safe Operating Area

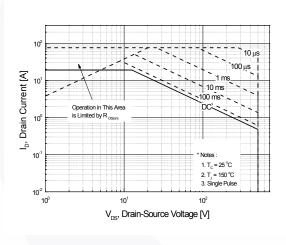


Figure 10. Maximum Drain Current vs. Case Temperature

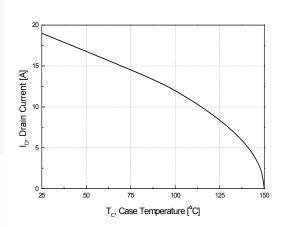


Figure 11. Transient Thermal Response Curve

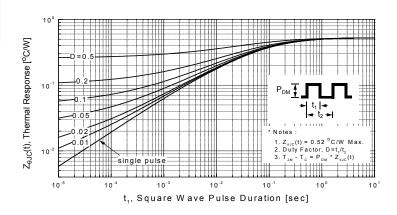


Figure 12. Gate Charge Test Circuit & Waveform

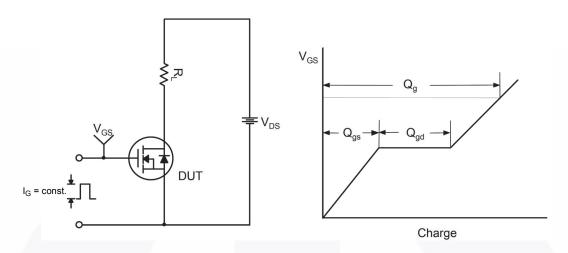


Figure 13. Resistive Switching Test Circuit & Waveforms

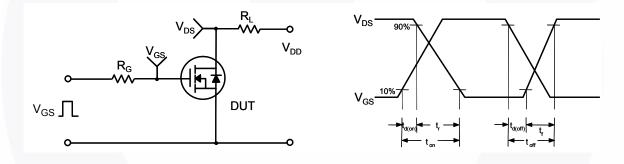
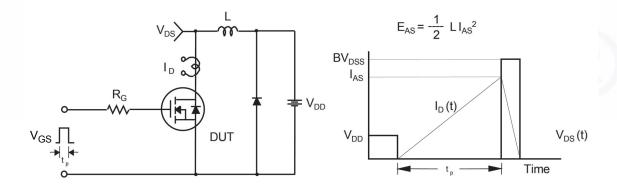


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



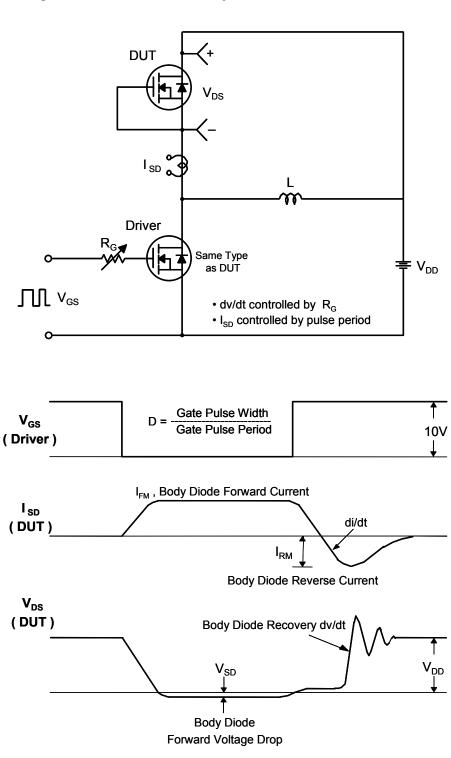
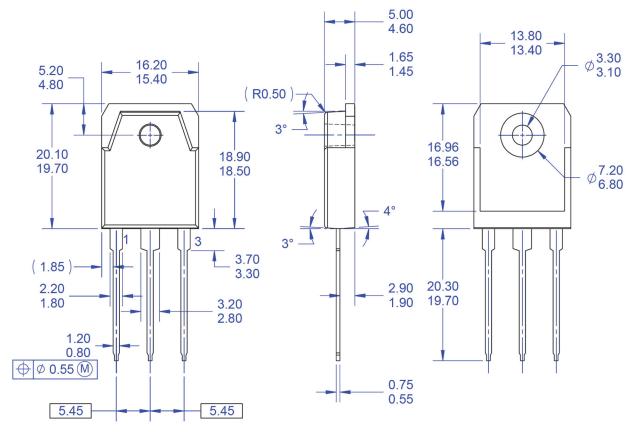
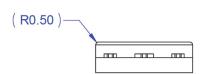


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions





NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- **DIMENSION AND TOLERANCING PER** ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.
 E) DRAWING FILE NAME: TO3PN03AREV1.
- FAIRCHILD SEMICONDUCTOR.

Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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